CD54HC173, CD74HC173, CD54HCT173, CD74HCT173

Data sheet acquired from Harris Semiconductor
SCHS158E

February 1998 - Revised October 2003

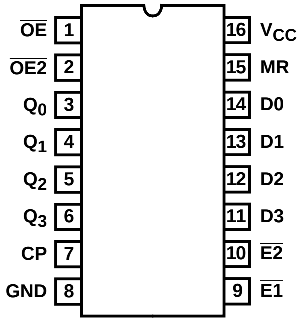
High-Speed CMOS Logic Quad D-Type Flip-Flop, Three-State

Features

- **Three-State Buffered Outputs**
- **Gated Input and Output Enables**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Pinout

CD54HC173, CD54HCT173
(CERDIP)
CD74HC173
(PDIP, SOIC, SOP, TSSOP)
CD74HCT173
(PDIP, SOIC)
TOP VIEW



Description

The 'HC173 and 'HCT173 high speed three-state quad D-type flip-flops are fabricated with silicon gate CMOS technology. They possess the low power consumption of standard CMOS Integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky devices. The buffered outputs can drive 15 LSTTL loads. The large output drive capability and three-state feature make these parts ideally suited for interfacing with bus lines in bus oriented systems.

The four D-type flip-flops operate synchronously from a common clock. The outputs are in the three-state mode when either of the two output disable pins are at the logic "1" level. The input ENABLES allow the flip-flops to remain in their present states without having to disrupt the clock If either of the 2 input ENABLES are taken to a logic "1" level, the Q outputs are fed back to the inputs, forcing the flip-flops to remain in the same state. Reset is enabled by taking the MASTER RESET (MR) input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

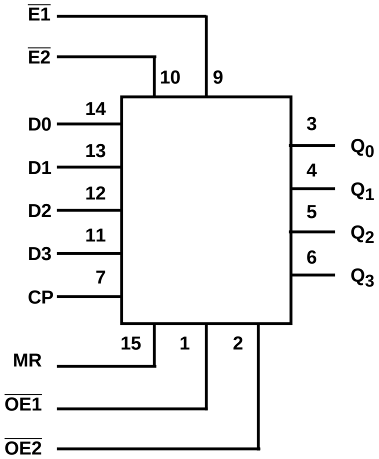
The 'HCT173 logic family is functionally, as well as pin compatible with the standard LS logic family.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC173F3A	-55 to 125	16 Ld CERDIP
CD54HCT173F3A	-55 to 125	16 Ld CERDIP
CD74HC173E	-55 to 125	16 Ld PDIP
CD74HC173M	-55 to 125	16 Ld SOIC
CD74HC173MT	-55 to 125	16 Ld SOIC
CD74HC173M96	-55 to 125	16 Ld SOIC
CD74HC173NSR	-55 to 125	16 Ld SOP
CD74HC173PW	-55 to 125	16 Ld TSSOP
CD74HC173PWR	-55 to 125	16 Ld TSSOP
CD74HC173PWT	-55 to 125	16 Ld TSSOP
CD74HCT173E	-55 to 125	16 Ld PDIP
CD74HCT173M	-55 to 125	16 Ld SOIC
CD74HCT173MT	-55 to 125	16 Ld SOIC
CD74HCT173M96	-55 to 125	16 Ld SOIC

NOTE: When ordering, use the entire part number. The suffixes 96 and R denote tape and reel. The suffix T denotes a small-quantity reel of 250.

Functional Diagram



TRUTH TABLE

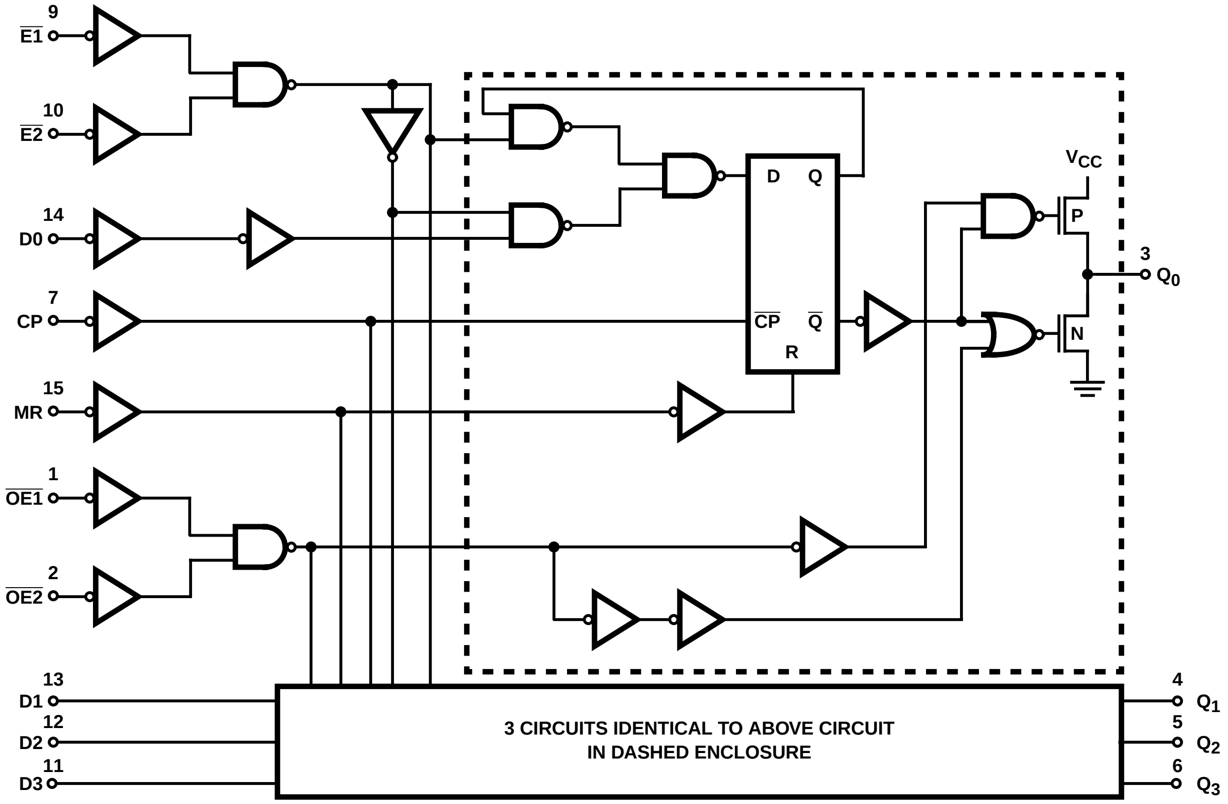
INPUTS				DATA	OUTPUT
		DATA ENABLE			
MR	CP	$\overline{E1}$	$\overline{E2}$	D	Q_n
H	X	X	X	X	L
L	L	X	X	X	Q_0
L	↑	H	X	X	Q_0
L	↑	X	H	X	Q_0
L	↑	L	L	L	L
L	↑	L	L	H	H

H= High Voltage Level
L = Low Voltage Level
X= Irrelevant
↑= Transition from Low to High Level
Q_0= Level Before the Indicated Steady-State Input Conditions Were Established

NOTE:

1. When either OE1 or OE2 (or both) is (are) high, the output is disabled to the high-impedance state, however, sequential operation of the flip-flops is not affected.

Logic Diagram



Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	±20mA
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	±20mA
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	±25mA
DC V_{CC} or Ground Current, I_{CC}	±70mA

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types	2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

Thermal Information

Package Thermal Impedance, θ_{JA} (see Note 2):	
E (PDIP) Package	67°C/W
M (SOIC) Package	73°C/W
NS (SOP) Package	64°C/W
PW (TSSOP) Package	108°C/W
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) (SOIC - Lead Tips Only)	300°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

2. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

		TEST CONDITIONS			25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	**SYMBOL**	**V_I (V)**	**I_O (mA)**	**V_{CC} (V)**	**MIN**	**TYP**	**MAX**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA

DC Electrical Specifications **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	6	-	-	±0.5	-	±0.5	-	±10	μA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 3)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

3. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
D0-D3	0.15
$\overline{E1}$ and $\overline{E2}$	0.15
CP	0.25
MR	0.2
$\overline{OE1}$ and $\overline{OE2}$	0.5

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Clock to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	200	250	300	ns
			4.5	-	40	50	60	ns
		C_L = 15pF	5	17	-	-	-	ns
		CL = 50pF	6	-	34	43	51	ns
Propagation Delay, MR to Output	t_{PHL}	C_L = 50pF	2	-	175	220	265	ns
			4.5	-	35	44	53	ns
		C_L = 15pF	5	12	-	-	-	ns
		CL = 50pF	6	-	30	37	45	ns
Propagation Delay Output Enable to Q (Figure 6)	t_{PLZ}, t_{PHZ} t_{PZL}, t_{PZH}	CL = 50pF	2		150	190	225	ns
		C_L = 50pF	4.5		30	38	45	ns
		C_L = 15pF	5	12	-	-	-	ns
		CL = 50pF	6		26	33	38	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	60	-	-	-	MHz
Input Capacitance	C_{IN}	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	29	-	-	-	pF
HCT TYPES								
Propagation Delay, Clock to Output	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	40	50	60	ns
		C_L = 15pF	5	17	-	-	-	ns
Propagation Delay, MR to Output	t_{PHL}	C_L = 50pF	4.5	-	44	55	66	ns
		C_L = 15pF	5	18	-	-	-	ns
Propagation Delay Output Enable to Q (Figure 6)	t_{PZL}, t_{PZH}	CL = 50pF	2		150	190	225	ns
		C_L = 50pF	4.5		30	38	45	ns
		C_L = 15pF	5	14	-	-	-	ns
		CL = 50pF	6		26	33	38	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	15	19	22	ns
Maximum Clock Frequency	f_{MAX}	C_L = 15pF	5	60	-	-	-	MHz
Input Capacitance	C_{IN}	-	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	34	-	-	-	pF

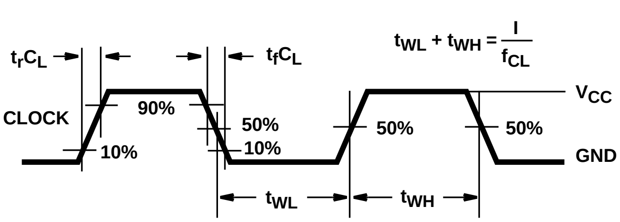
NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per package.
5. $P_D = V_{CC}^2 f_i + \sum (C_L V_{CC}^2 + f_O)$ where f_i = Input Frequency, f_O = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Prerequisite For Switching Specifications

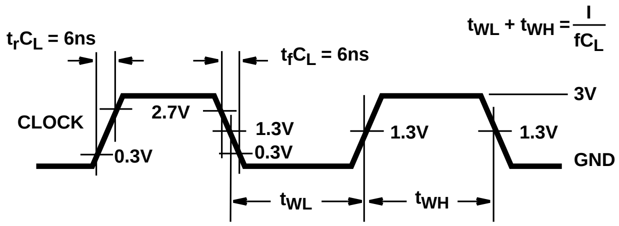
PARAMETER	SYMBOL	V_{CC} (V)	25°C		-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	
HC TYPES									
Maximum Clock Frequency	f_{MAX}	2	6	-	5	-	4	-	MHz
		4.5	30	-	24	-	20	-	MHz
		6	35	-	28	-	24	-	MHz
MR Pulse Width	t_W	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Clock Pulse Width	t_W	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Set-up Time, Data to Clock and $\overline{E}$ to Clock	t_{SU}	2	60	-	75	-	90	-	ns
		4.5	12	-	15	-	18	-	ns
		6	10	-	13	-	15	-	ns
Hold Time, Data to Clock	t_H	2	3	-	3	-	3	-	ns
		4.5	3	-	3	-	3	-	ns
		6	3	-	3	-	3	-	ns
Hold Time, $\overline{E}$ to Clock	t_H	2	0	-	0	-	0	-	ns
		4.5	0	-	0	-	0	-	ns
		6	0	-	0	-	0	-	ns
Removal Time, MR to Clock	t_{REM}	2	60	-	75	-	90	-	ns
		4.5	12	-	15	-	18	-	ns
		6	10	-	13	-	15	-	ns
HCT TYPES									
Maximum Clock Frequency	f_{MAX}	4.5	20	-	16	-	13	-	MHz
MR Pulse Width	t_W	4.5	15	-	19	-	22	-	ns
Clock Pulse Width	t_W	4.5	25	-	31	-	38	-	ns
Set-up Time, $\overline{E}$ to Clock	t_{SU}	4.5	12	-	15	-	18	-	ns
Set-up Time, Data to Clock	t_{SU}	4.5	18	-	23	-	27	-	ns
Hold Time, Data to Clock	t_H	4.5	0	-	0	-	0	-	ns
Hold Time, $\overline{E}$ to Clock	t_H	4.5	0	-	0	-	0	-	ns
Removal Time, MR to Clock	t_{REM}	4.5	12	-	15	-	18	-	ns

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

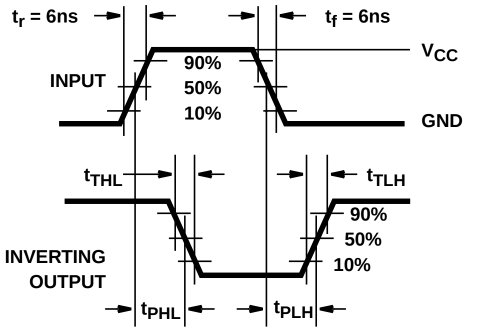


FIGURE 3. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

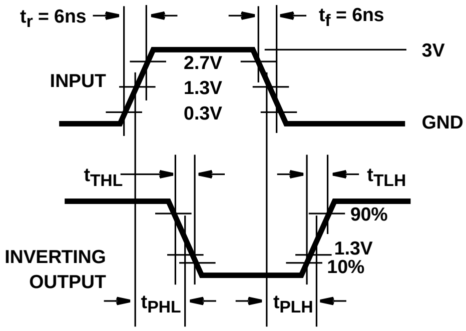


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

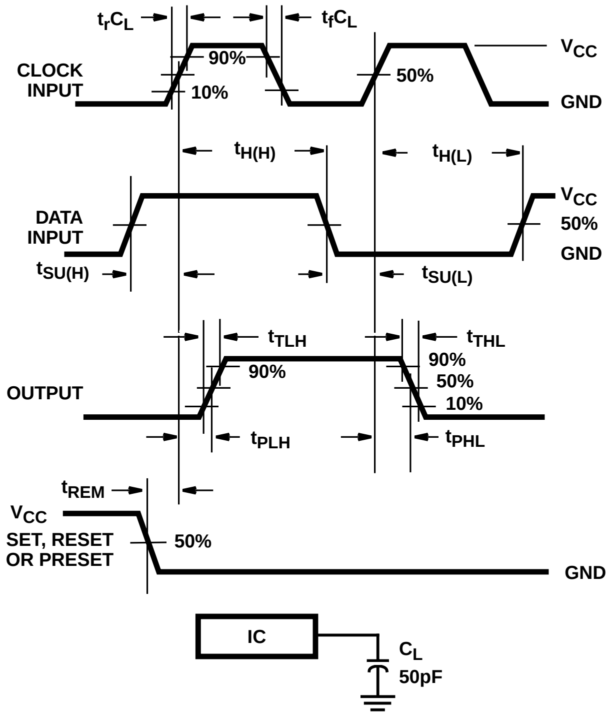


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

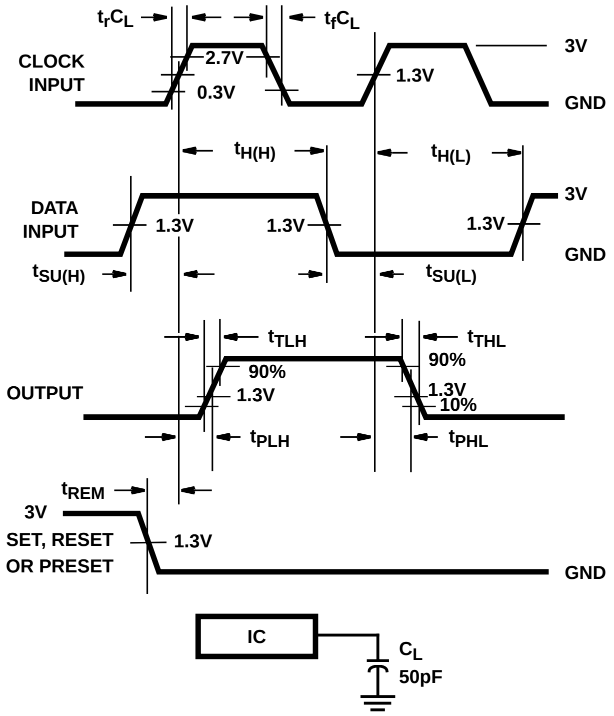


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

Test Circuits and Waveforms (Continued)

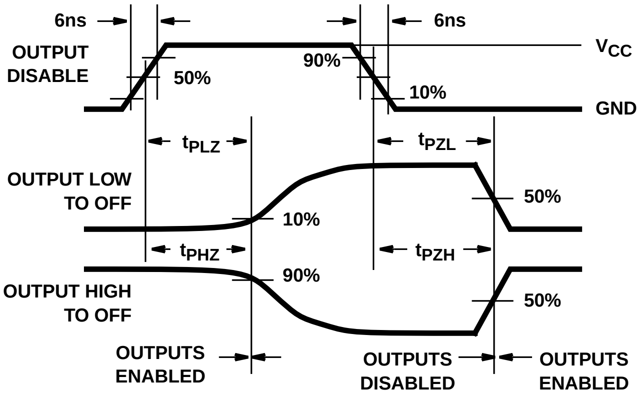


FIGURE 7. HC THREE-STATE PROPAGATION DELAY WAVEFORM

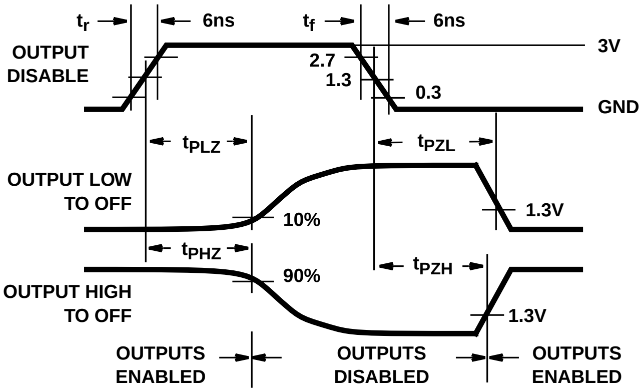
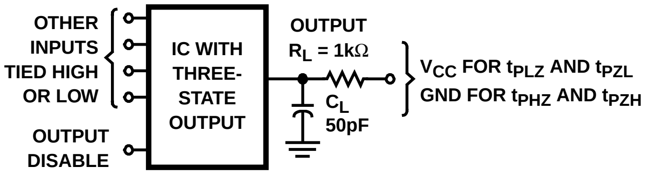


FIGURE 8. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC}, $C_L = 50pF$.

FIGURE 9. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT